NSN 5961-01-129-1967

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-129-1967 **Inclosure Material:** Metal and glass **Overall Length:** Between 0.170 inches and 0.210 inches **Terminal Length:** 1.500 inches **Overall Diameter:** Between 0.209 inches and 0.230 inches **End Application:** T-39a 99999 **Internal Configuration:** Field effect **Mounting Method: Terminal Terminal Circle Diameter:** 0.100 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 15.0 drain to source voltage and 15.0 drain to gate voltage **Current Rating Per Characteristic:** 50.00 milliamperes gate current **Power Rating Per Characteristic:** 300.0 milliwatts total device dissipation **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Terminal Type And Quantity:** 4 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:**

Yes - demil/mli

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